

# EVVOSEMI<sup>®</sup>

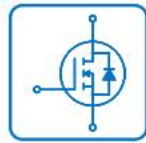
THINK CHANGE DO



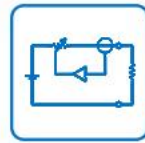
ESD



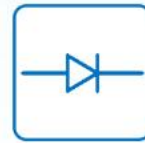
TVS



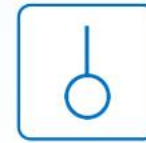
MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

▶ Domestic	Part Number	AO4828
▶ Overseas	Part Number	AO4828
▶ Equivalent	Part Number	AO4828

EV is the abbreviation of name EVVO

## Dual N-Channel MOSFET

### Description

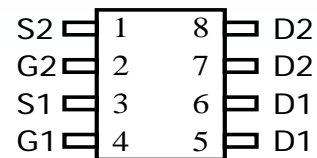
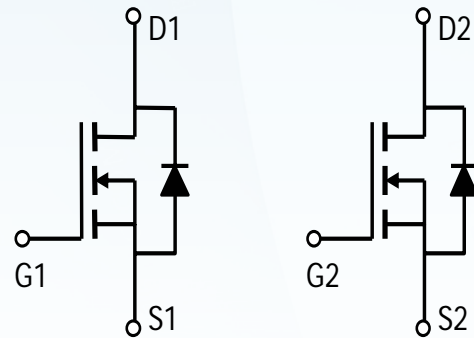
The AO4828 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

$V_{DS} = 60V$   $I_D = 6.5A$   
 $R_{DS(ON)} < 36m\Omega @ V_{GS}=10V$   
 $R_{DS(ON)} < 47m\Omega @ V_{GS}=4.5V$

### Application

Battery protection  
 Load switch  
 Uninterruptible power supply



### Absolute Maximum Ratings@ $T_J=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A=25^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	6.5	A
$I_D @ T_A=70^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	30	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation	2.1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	60	$^\circ C/W$

## Dual N-Channel MOSFET

### Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	69	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=6A$		30	36	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$		36	47	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=6A$		20	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$		1920		PF
Output Capacitance	$C_{oss}$			155		PF
Reverse Transfer Capacitance	$C_{rss}$			116		PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=30V, R_L=4.7\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	8	-	nS
Turn-on Rise Time	$t_r$		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	nS
Turn-Off Fall Time	$t_f$		-	6	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=30V, I_D=6A,$ $V_{GS}=10V$	-	50	-	nC
Gate-Source Charge	$Q_{gs}$		-	8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	16	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=6A$	-	-	1.2	V
Diode Forward Current	$I_S$		-	-	7	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = 7A$	-	35	-	nS
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$ (Note 3)	-	43	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

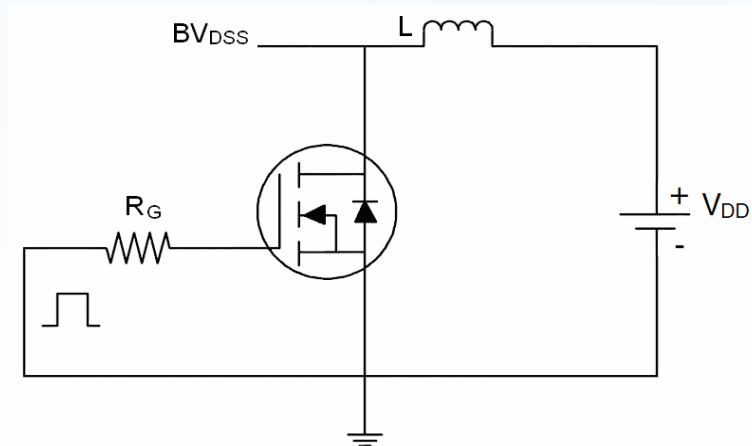
#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

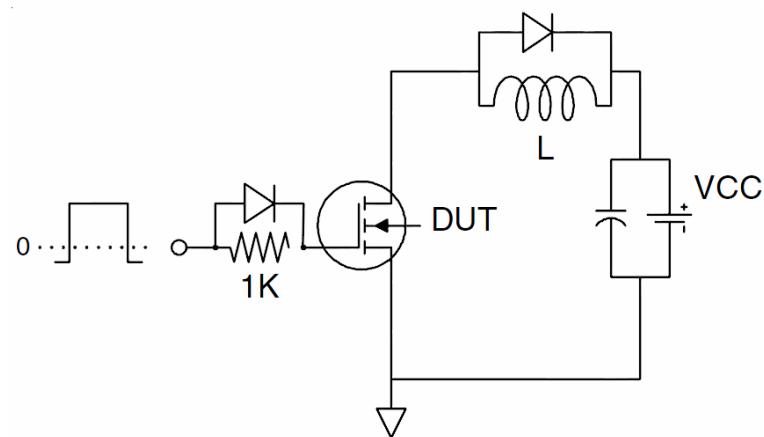
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Test Circuit

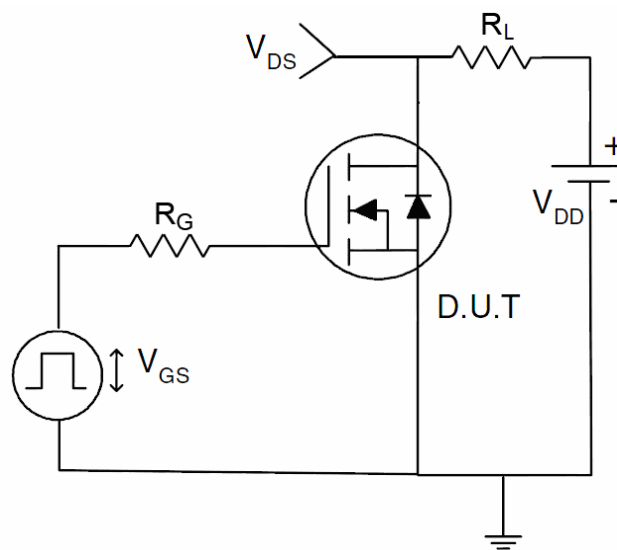
1) E<sub>AS</sub> test Circuits



2) Gate charge test Circuit



3) Switch Time Test Circuit



Dual N-Channel MOSFET

Typical Electrical and Thermal Characteristics (Curves)

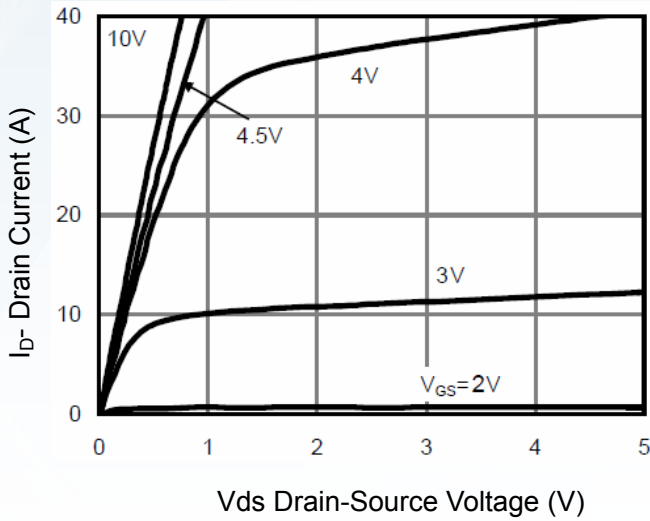


Figure 1 Output Characteristics

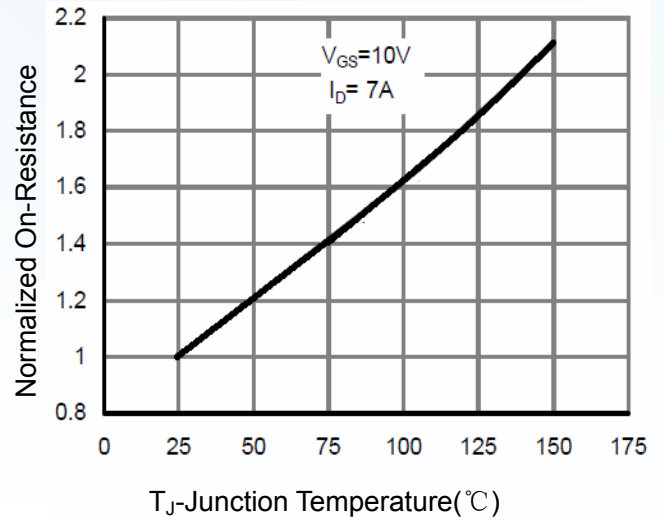


Figure 4  $R_{dson}$ -Junction Temperature

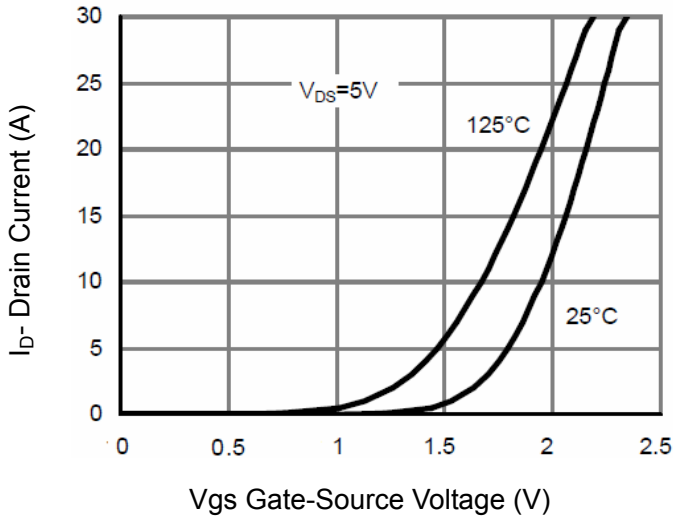


Figure 2 Transfer Characteristics

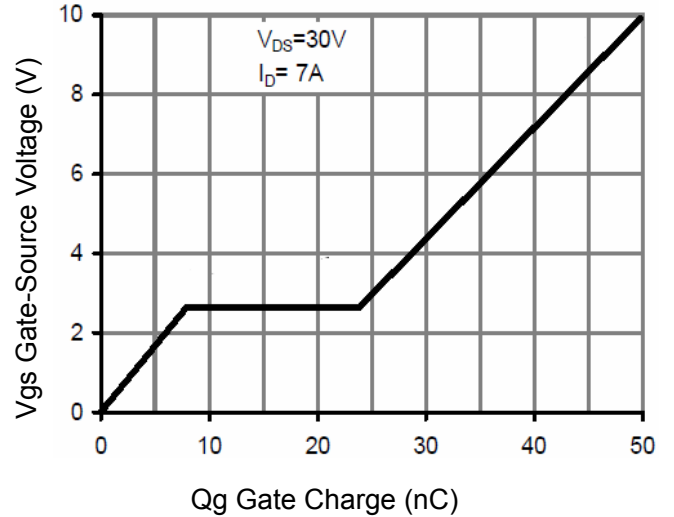


Figure 5 Gate Charge

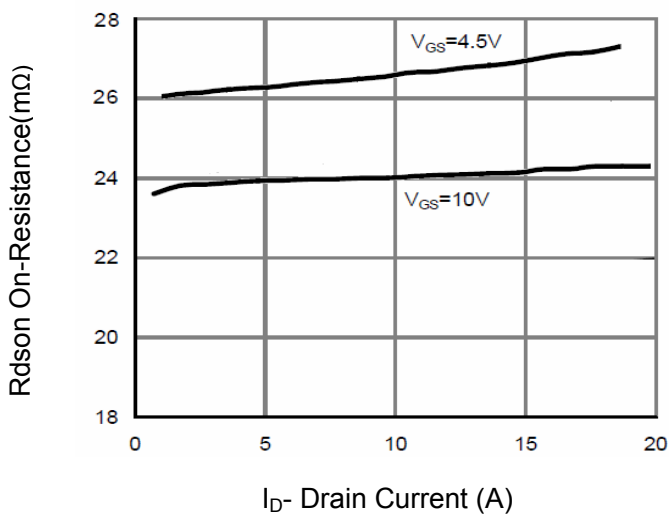


Figure 3  $R_{dson}$ - Drain Current

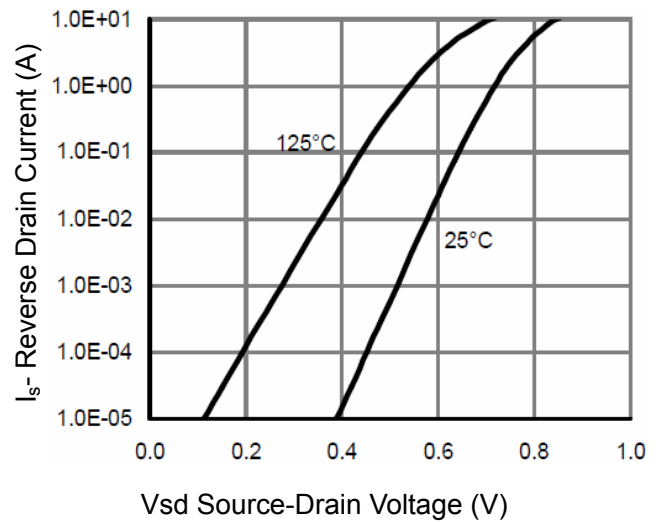
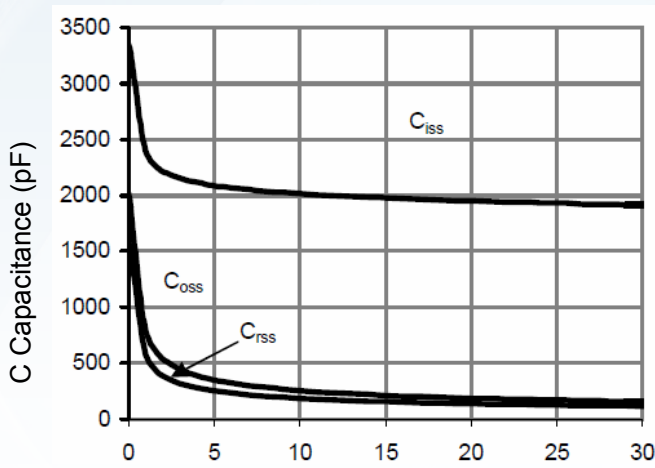
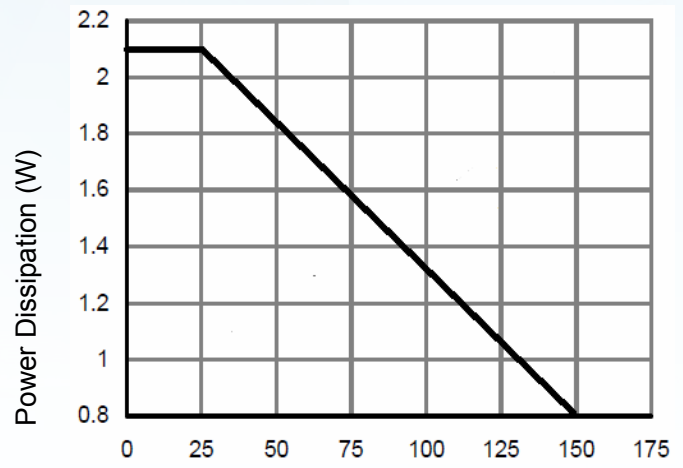


Figure 6 Source- Drain Diode Forward

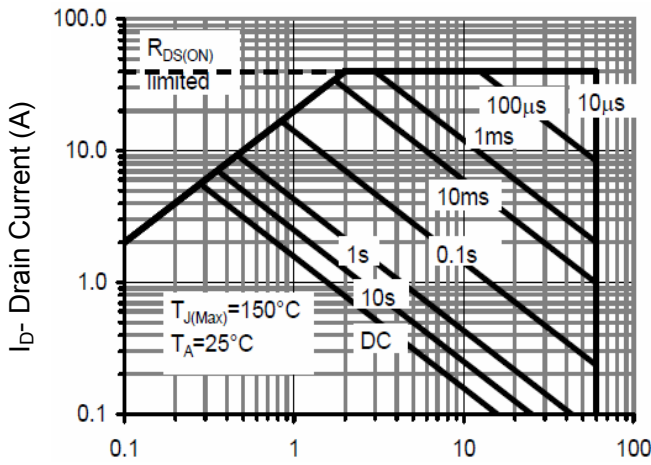
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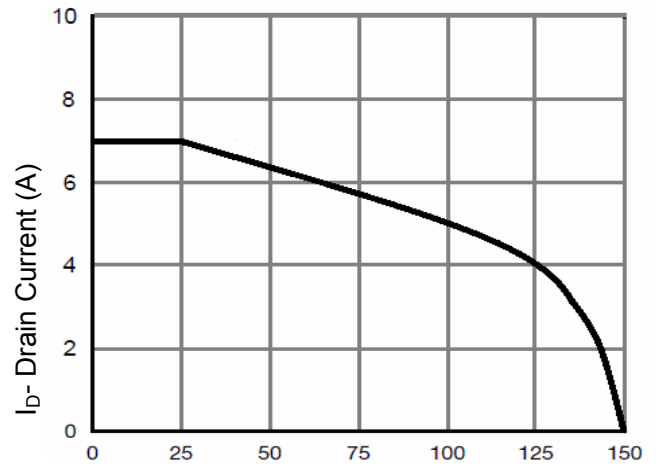
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



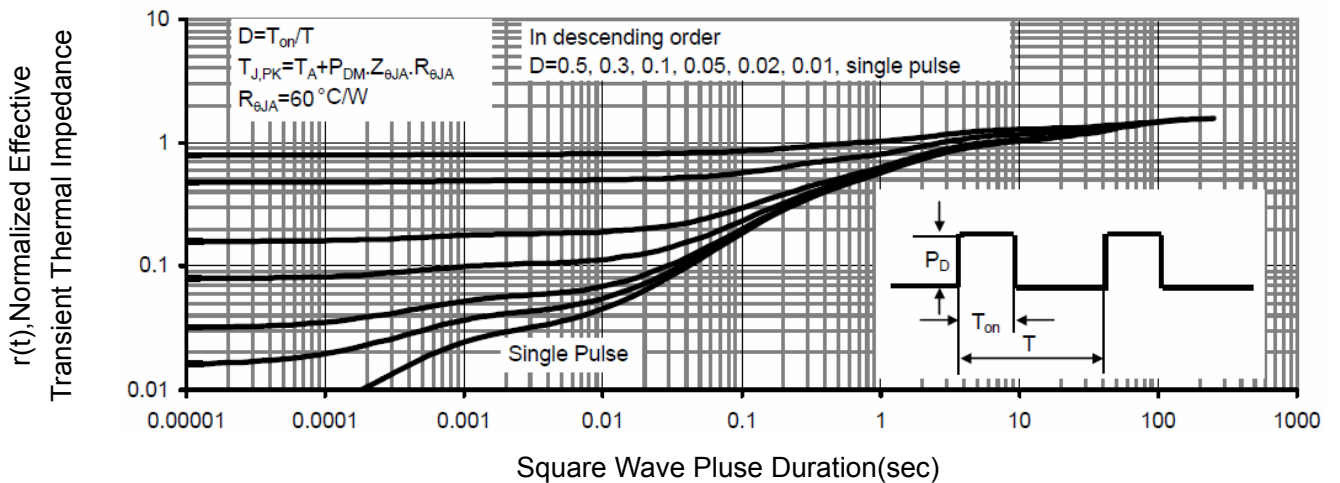
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 9 Power De-rating**



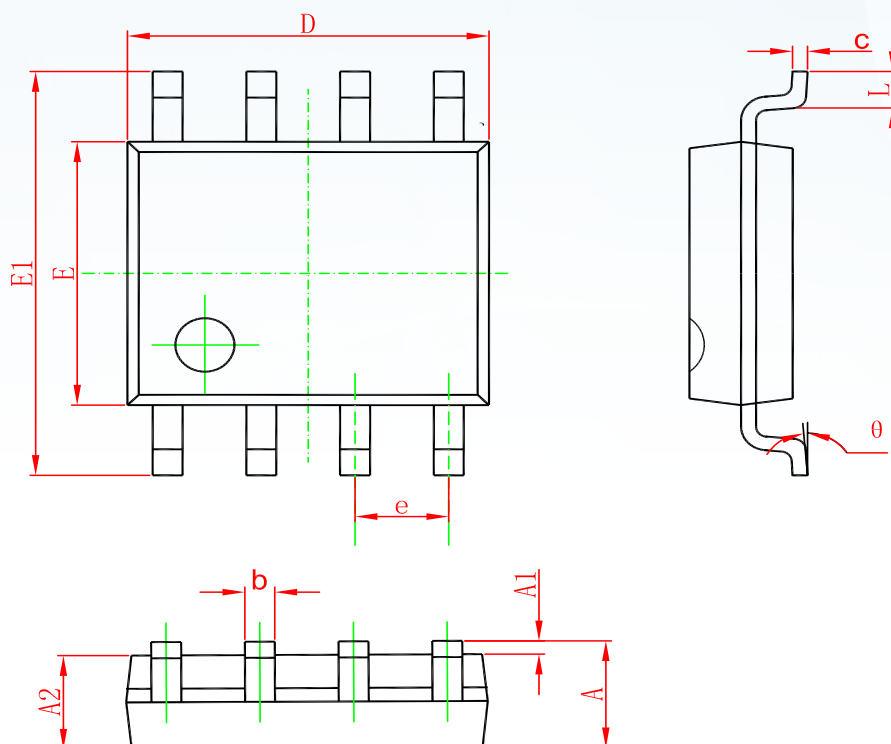
Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**



T<sub>J</sub>-Junction Temperature(°C)  
**Figure 10 Current De-rating**



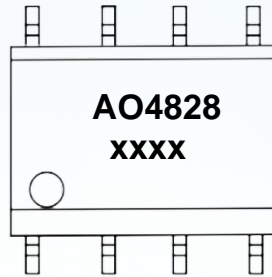
**Figure 11 Normalized Maximum Transient Thermal Impedance**

**Dual N-Channel MOSFET**
**PACKAGE OUTLINE DIMENSIONS**
**SOP-8**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## Dual N-Channel MOSFET

### Marking



("xxxx"代表年份周期)

### Ordering information

Order code	Package	Baseqty	Deliverymode
AO4828	SOP-8	3000	Tape and reel



## Disclaimer

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